

REMARKS

This application has been carefully reviewed in light of the Office Action dated April 28, 2004. Claims 1 to 15 are in the application, with Claim 1 being independent. Claims 1, 2, 6, 8, 9 and 12 have been amended herein. Claim 15 has been newly added. Reconsideration and further examination are respectfully requested.

Claims 1 to 14 were rejected under 35 U.S.C. § 102(b) over U.S. Patent No. 5,453,135 (Nakagawa). The rejection is respectfully traversed.

Claim 1 recites, *inter alia*, a process for forming on a substrate a transparent conductive film having crystallizability, the process comprising a first step of forming a film at a first film formation rate and a second step of forming a film at a second film formation rate.

Nakagawa is not seen to teach or suggest at least the foregoing combination of features.

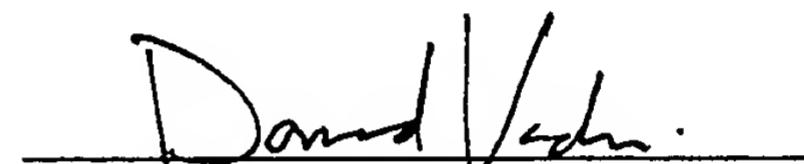
According to the Office Action, Nakagawa's layer 204 corresponds to the transparent conductive film of the present invention. However, Applicants respectfully submit that the layer 204 is not a transparent conductive film having crystallizability. As described at col. 22, lines 26 to 28 of Nakagawa, the layer 204 is a thin film active semiconductor region. Nakagawa uses the reference numeral 203 for his transparent conductive film.

The dependent claims are also submitted to be patentable because they set forth additional aspects of the present invention and are dependent from the independent claim discussed above. Therefore, separate and individual consideration of each dependent claim is respectfully requested.

Applicants submit that this application is in condition for allowance, and a Notice of Allowance is respectfully requested

Applicants' undersigned attorney may be reached in our Washington, D.C. office by telephone at (202) 530-1010. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,



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